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1	Vít Malinovsky, "System Macromodel of Agricultural Building with Aim to Energy Consumption Minimization", <i>Agris On-Line Papers in Economics & Informatics</i> . Mar2018, Vol. 10 Issue 1, p25-35. 11p, https://scholar.google.ro/scholar?oi=bibs&hl=ro&ites=14433228815614064465	Scopus	7		0.571
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1	C.-Y.Ahn, J.-S. Kim, "Analysis of ZCS operation characteristics of GaN FET-based IPT system", (2020) 69 (9), pp. 1356-1363, https://www.scopus.com/inward/record.uri?eid=s2-0-85091464424&doi=10.5370%2fKIEE.2020.69.9.1356&partnerID=40&md5=ad21461a71ab6c750045bb58ee162294 , DOI: 10.5370/KIEE.2020.69.9.1356	Scopus	6		0.667
	A3.2 Membru în colective de redacție sau comitete științifice ale revistelor indexate ISI, chair, co-chair sau membru în comitetele de organizare ale manifestărilor științifice internaționale indexate ISI [9]	Baza de date	[9]		
1	Membru al Paper Review Board International Semiconductor Conference - CAS, Sinaia, Romania, din 2011	ISI			10.000
2	Membru in International Steering Committee, SIITME, Oradea 2016	ISI			10.000
3	Chairman la International Semiconductor Conference - CAS, Sinaia, Romania, din 2013	ISI			10.000

4	Recenzie ECSCRM 2012	ISI			10.000
5	Associate Editor, ROMJIST, din 2017	ISI			10.000
6	Recenzor SENSORS, 2019	ISI-Q1			10.000
7	Recenzor JAP 2019	ISI-Q2			10.000
	A3.3 Membru în colective de redacție sau comitete științifice ale revistelor indexate BDI, chair, co-chair sau membru în comitetele de organizare ale manifestărilor științifice internaționale indexate BDI [9]	Baza de date			
1	Recenzii la Revista Buletin Științific al Universității Politehnica din Bucuresti, din 2019	Scopus			6.000
	A3.4 Premii în domeniu conferite de Academia Română, ASTR, AOSR, sau premii internaționale de prestigiu				
	Total A3				300.290

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